World's Third Largest Chipmaker



176-Layer 4D NAND Flash

Innovation to proven, stable technology for 5G smartphones

SK hynix

uMCP

SK hynix UFS2.2 (UD220)

SK hynix UFS3.1

SK hynix's 4D NAND Flash

- 4D NAND is the Tech Platform strategy that maximizes storage capacity by forming peripheral circuits under the cell, using the periphery under cell (PUC) technology.
- Since announcing the industry's first 96-layer 4D NAND platform in 2018, SK hynix followed up with a 128-layer 4D NAND flash in 2019, another industry-first.



SK hynix's 176-Layer NAND Flash

- The industry's tallest, 176–layer NAND also utilizes the 4D NAND platform.
- Built on the mature 4D NAND platform used since the 96-layer stack, the technology is highly reliable.





Features of SK hynix's 176-Layer(V7) UFS

Space-efficient Package

- Package shrink to 11x13mm in line with demand for smaller chips in 5G smartphones
- Stronger performance in smaller and thinner package



Better Power Consumption

Greater power efficiency, generating higher performance than 128-layer(V6) flash with the same amount of power





176-Layer(V7) Mobile Memory Performance



UFS3.1 (UD310)



UFS2.2 (UD220)









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